

**PATENT APPLICATION**

Sheet 1 of 5

<b>FORM PTO-1449</b>  <b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>  (Use several sheets if necessary)	ATTY. DOCKET NO.	APPLICATION NO.	CONFIRMATION NO.
	<b>200206465-1</b>		
	APPLICANT		
	<b>Ashton, et al</b>		
	FILING DATE	GROUP	
	<b>Sept. 26, 2003</b>		

**REFERENCE DESIGNATION**

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
TT	1A	5,557,596	09/17/96	Gibson et al	
TT	1B	6,256,224	07/03/01	Perner, et al.	
TT	1C	6,262,421	07/17/01	Tran	
	1D				
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	1L					
	1M					
	1N					
	1O					
	1P					

**OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)**

TT	1Q	Kampmann, et al. A Cadmium-free CuInSe <sub>2</sub> Superstrate Solar Cell Fabricated by Electrodeposition Using a ITO/In <sub>2</sub> Se <sub>3</sub> /CuInSe <sub>2</sub> /Au Structure; Progress in Photovoltaics; (1999) pgs. 129-135.
TT	1R	Rechid, et al. Characterising Superstrate CIS solar cells with electron beam induced current; Thin Solid Films; (2000) pgs. 361-362.
TT	1S	Ward, et al. Cu(In,Ga)Se <sub>2</sub> Thin-Film Concentrator Solar Cells; NCPV Program Review Meeting; 10/01.

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*[Signature]*

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<b>FORM PTO-1449</b>  <b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>  (Use several sheets if necessary)	ATTY. DOCKET NO. <b>200506465-1</b>	APPLICATION NO.	CONFIRMATION NO.
	APPLICANT <b>Ashton, et al</b>		
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<i>TT</i>	2Q	Scofield, et al. Sputtered molybdenum bilayer back contact for copper indium diselenide-based polycrystalline thin-film solar cells; Thin Solid Films (1995) pgs. 26-31
<i>TT</i>	2R	Gabor, et al. High-efficiency CuIn <sub>x</sub> Ga <sub>1-x</sub> Se <sub>2</sub> solar cells made from (In <sub>x</sub> Ga <sub>1-x</sub> ) <sub>2</sub> Se <sub>3</sub> precursor films; American Institute of Physics, (1994) pgs. 198-200
<i>TT</i>	2S	Nakayama, et al. AES, LEELS and XPS studies on the interface formation between layered semiconductors GaSe and InSe; Surface Science (1991)

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TT	3Q	Nishida, et al. Single-beam overwrite experiment using In-Se based phase-change optical media; American Institute of Physics (1987) pgs. 667-669
TT	3R	Sanchez-Royo, et al. Optical and photovoltaic properties of indium selenide thin films prepared by van der Waals epitaxy; Journal of Applied Physics (2001) pgs. 2818-2823
TT	3S	Otsmane, et al. Epitaxy of layered semiconductor thin films; Applied Surface Science (1993) pgs. 479-481

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TT	4Q	Emery, et al. Reflection high-energy electron diffraction studies of InSe and GaSe layered compounds grown by molecular beam epitaxy; Journal of Applied Physics (1992) pgs. 3256-3259
TT	4R	Tatsuyama, et al. Heteroepitaxy between layered semiconductors GaSe and InSe; Applied Surface Science (1989) pgs. 539-543
TT	4S	Gashimzade, et al. Energy spectrum and effective mass of carriers in the InSe/GaSe superlattice; Z. Physics (1996) pgs. 219-222

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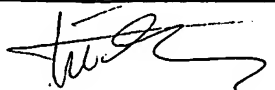
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	5P					

## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

TT	5Q	Shigetomi, et al. Electrical and photovoltaic properties of Cu-doped p-GaSe/n-InSe heterojunction; Journal of Applied Physics; (2000); pgs. 1520-1524
	5R	
	5S	

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